Femtosecond LIPSS on indium-tin-oxide thin films at IR wavelengths

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Abstract: We performed the experimental and numerical investigation of laser-induced periodic surface structures (LIPSS) generated on indium-tin-oxide (ITO) thin films with femtosecond laser pulses in the infrared region. Using pulses between 1.6 and 2.4 µm central wavelength, we observed robust LIPSS morphologies with a wavelength-independent periodicity of 220 ± 20 nm. Supporting finite-difference time-domain calculations suggest that the surface forms are rooted in the field localization in the surface pits leading to a periodically increased absorption of the laser pulse energy that creates the observed periodic structures. Thus, the LIPSS process is independent of the pulse parameters and it is only determined by the sample used.

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1. Introduction

Indium-tin-oxide (ITO) is one of the most widely used conducting oxides due to its high electrical conductivity and broad spectral transmission from the visible to the infrared range. Deposited in the form of thin surface film, it can serve as a transparent electrode or conductive layer in nanoplasmonic experiments [1], electrochemical systems [2], photovoltaic devices [3-5] or even biosensors for virus detection [6]. Previously it was shown that the surface of an ITO thin film can be patterned with ultrashort laser pulses and certain characteristics of the treated areas can be altered. Many of these comparative studies investigated the laser-induced periodic surface structure (LIPSS) generation both experimentally and theoretically. Based on the periodicity of these structures compared to the laser wavelength, they can be divided into two categories: I. In the case of low-spatial-frequency LIPSS (LSFL), the laser wavelength and the periodicity of the generated structures are on the same order of magnitude and the periodicity is perpendicular to the laser polarization. II. The periodicity of the high-spatial-frequency LIPSS (HSFL) is considerably smaller than the applied laser wavelength and these structures are usually parallel to the laser polarization.

The formation mechanism of LIPSS generated by ultrafast laser pulses with different wavelengths and pulse durations has been extensively examined in recent years. It is generally accepted that the LSFL generation is caused by the interaction of the incident laser field and the electromagnetic wave on the surface formed by the initially rough surface [7, 8]. The interference of these waves distorts the spatial field distribution along the surface, thus forming a periodic intensity pattern that leads to the corresponding ablation of the ITO. For HSFL, the formation mechanism is usually explained by the self-organization of the melted material [9], second harmonic order waves along the surface [10] and splitting of longer period ripples of LSFL [11]. Another widely accepted process that has been discussed previously is based on light scattering on locally created nanosized holes in the sample surface [12]. Similar craters appear in the ITO after a few pulses where the surface morphology has local discontinuities. Subsequent pulses interacting with these defects result scattered waves that interfere with each
other, hence forming an intensity pattern that leads to the HSFL ripples. Also, the formation of periodic structures on glass surface under the ITO or ZnS layer was reported before [14, 15]. In these cases, it was found that the underlying glass surface could be nano-fabricated using fluences amounting to ~25% of the ablation threshold of the glass. It was proposed that the LIPSS formation was determined by the dielectric constant of ZnS in the excited state under laser excitation. Laser-induced surface electric field enhancement and energy delivery explained the formation of periodic LIPSS on the silica substrate.

Irradiating a 180 nm thick ITO film on a glass substrate with 532 nm, 10 ps pulses at 1 kHz repetition rate resulted in HSFLs with periodicity around, and even below 200 nm [11]. Calculations were carried out regarding the surface ablation topology and LIPSS formation of the ITO film during pulse propagation to support the experimental results. Another study dealt with 800 nm wavelength, 50 fs pulses at 1 kHz repetition rate on a 175 nm thick ITO layer on glass substrate with cylindrical lens to create LIPSS formations on the ITO while scanning the sample [13]. HSFLs appeared with orientation perpendicular to the laser polarization and FFT analysis of the SEM images confirmed periodicity between 150 and 250 nm. The analysis of the FFT spectra also concludes that at lower fluences the generated HSFLs are much less regular than the ones created at higher fluences. Using 1032 nm, 10 ps laser pulses at 400 kHz on a 175 nm thick ITO film on glass substrate enabled the investigation of the evolution of subwavelength surface nanoripples [16]. The generated LIPSS had a perpendicular orientation relative to the laser polarization for a small number of applied pulses (<5) and the periodicity that was measured to be between 115 and 345 nm, depending on the size and distribution of the nanoblisters.

Overall, the LIPSS formation of ITO covered glass substrates was investigated at many wavelengths in the visible and near-infrared range at a large variety of pulse durations. The reported periodicities and the resulting morphologies are similar and show negligible dependence on the incident laser wavelength. This suggests that the formation of the HSFL morphologies and the resulted periodicities could be connected to some fundamental parameter of the ITO itself. To verify this hypothesis, we set out to conduct a comparative study that explores the generated LIPSS formations produced by different wavelength femtosecond laser pulses in the infrared regime.

Therefore, in this paper, we investigate LIPSS formations by back illuminating a 150 nm thick ITO film deposited on a fused silica substrate using 70 fs laser pulses with 1.6, 2.0 and 2.4 μm wavelengths. The resulting periodic structures on the surface of the ITO and the underlying glass are compared to our finite difference time domain (FDTD) simulations to understand the processes behind nanostructure formation and its evolution.

2. Experimental setup and methods

In our experiments, we used a regenerative Ti:sapphire amplifier (Coherent Legend Elite) seeded with a home-built oscillator. The 800 nm, 50 fs output pulses with 10 kHz repetition rate were directed into an optical parametric amplifier (OPA) with a 70-fs output pulse length, and controllable output wavelength between 300 nm and 15 μm. The sample was a 150 nm thick ITO layer deposited onto a 1 mm fused silica substrate. These infrared pulses were focused by back-illumination to the ITO-glass interface by a 200 mm focal length CaF₂ lens, resulting a focal spot with 260 μm diameter. All LIPSS generation experiments were conducted in ambient air environment. Pulse energies were controlled by a set of discrete neutral density filters. In the investigated wavelength range, the ITO absorption increases drastically: at 1.6 μm it is 33 %, at 2.0 μm it is 65 % and at 2.4 μm it is 75 %. Considering this behavior of the ITO, the absorbed pulse energy is higher at longer wavelengths, which was compensated by using less energetic pulses for longer wavelengths. Illumination times of between 1 s and 5 s were used and the duration was set by a controllable shutter. Due to the subsequent nonlinear
processes in the OPA, negligibly low energy pulses with longer duration in the visible range were also present at the output besides the infrared pulses used to generate the LIPSSs. These pulses did not contribute to the periodic structure generation processes but were used to monitor the LIPSS formation by detecting the scattered light from the modified surface with a CCD camera.

![Experimental setup](image)

**Fig 1.** Experimental setup with femtosecond light source (LS), tunable optical parametric amplifier (OPA), programmable shutter (SH), neutral density filter (ND), focusing lens (L), ITO covered glass sample (S) and CCD camera (C). Inset: back-illuminated focusing geometry with normalized electric field distribution and measured spectra of the used beams.

The laser-treated areas and the formed LIPSSs were inspected with a scanning electron microscope (TESCAN MIRA3 SEM). To resolve the surface morphology, the in-beam secondary electron detector was chosen with 5 kV accelerating voltage. The images were acquired via line accumulation with 4 mm working distance and a magnification between 2400 and 160 000. To gather information about the composition and to examine the amount of ITO ablated from the surface, we also performed element analysis in the laser-treated areas. Before the LIPSS experiments, the surface of the original, untreated ITO layers was also investigated with a PSIA XE-100 atomic force microscope in dynamic, non-contact mode over 5 μm × 5 μm and 20 μm × 20 μm scanning areas. The average roughness was determined by the manufacturer's (XEI) software.

### 3. Femtosecond LIPSS results in the infrared

Fig. 2. shows SEM images of the resulted surface morphologies after 0.1 s exposition with pulse energies between 9 and 15 μJ.
The 0.1 s illumination with infrared pulses resulted in cracks on the ITO surface in the case of all three wavelengths. The orientation of these cracks does not show any dependence on the laser polarization and does not follow the initial ITO morphology. This suggests that the origin of these fractures is the heat stress caused by the rapid heating of the laser-treated area due to the absorbed energy of the laser pulses. Fig. 2(a-c) also show the presence of few nanometers sized craters where the ITO got completely removed from the glass substrate. These can be explained by the following: As the fractures form on the surface, regions, where the initial ITO cohesion is weaker, get separated from the surrounding material and get rejected from the surface due to the buildup of local electrostatic charge. It can be also observed that apart from these fractures and craters, the ITO surface morphology remained intact, there are no signs of any melting and resolidification processes. These changes of the ITO surface pave the way for more prominent surface modifications of subsequent pulses.

SEM images of the generated LIPSS formations in the case of 1 s exposition with pulse energies between 9 and 15 µJ are shown in Fig. 3.

As shown in Fig. 3(a) using 1.6 µm pulses, cracks appear on the surface of the ITO with an orientation perpendicular to the laser polarization. Close to the center of the focal spot in the highest local intensity region several randomly arranged craters are present with sizes between 150 and 500 nm. The interference of light scattered from these craters may explain the periodic structures generated at higher pulse energies [12].

In the case of 2 µm and 2.4 µm pulses where the absorption of the ITO is higher, periodic melting patterns appear forming HSFLs perpendicular, and LSFLs parallel to the laser polarization. The LSFLs created by 2-µm pulses are irregular, and they become more distinct
in the case of 2.4 µm illumination. The periodicity of these structures is close to 2 µm based on the SEM images, showing no wavelength dependence whatsoever. Around the structured area created by 2 µm pulses, a transition zone can be observed where the lower local intensity creates nanosized craters similar to the ones generated by the 1.6 µm pulses. This transition zone disappears in the case of 2.4 µm illumination.

The generated HSFL formations for all three wavelengths are shown in Figs. 4(a-c) with higher magnification.

![Detailed SEM images of the HSFL formations in case of a) 1.6 µm and 3.8 \times 10^{11} W/cm², b) 2.0 µm and 2.3 \times 10^{11} W/cm², c) 2.4 µm and 2 \times 10^{11} W/cm² peak intensity pulses. Inset figures show the FFT inverse-space spectra of the SEM images unveiling real space periodicity.](image)

The periodicity of the HSFLs was calculated by applying a 2-dimensional fast Fourier transform (FFT) to the SEM images. Based on the FFT inverse-space spectra, the periodicity of the HSFLs is between 200 and 240 nm for all wavelengths. The surface morphology of the structures is smoother than the intact ITO pattern. This fact, and the presence of melted ITO droplets seen in Figs. 4(b) and 4(c) suggest that these structures can be originated from a melting process occurring during the longer exposition time.

Longer expositions with higher pulse energies result in the ablation of the ITO in the center of the focal spot. Fig. 5(a) shows the laser treated area after 5 s exposition of 2-µm pulses with 15 µJ pulse energy.

![Fig 5. a) SEM image of the laser treated area color-mapped with the local peak intensity using 2-µm wavelength, 3.8 \times 10^{11} W/cm² peak intensity pulses with 5 s illumination. For a description of areas I-VI, see manuscript Table 1. b) Tilted SEM image of the HSFL formations of the ITO and the structured underlying glass generated with 2\mu m wavelength, 2.3 \times 10^{11} W/cm² peak intensity pulses with 1 s illumination.](image)
Different types of typical morphologies around the focal spot can be classified as follows: I. At lower peak intensities the ITO starts to crack due to the thermal stress caused by higher thermal gradient. II. At higher peak intensities, smaller craters appear, and a primary periodicity perpendicular to the electric field can be seen comparable to the one in Fig. 3(a). III. Increasing the peak intensity these vertical stripes start to separate from each other creating HSFL with a periodicity of 200 – 240 nm perpendicular to the laser polarization. IV. Closer to the focal spot, the secondary LSFL is formed with a periodicity around 2 μm, matching the laser wavelength. V. Close to the center of the focal spot the ITO is almost fully ablated from the glass substrate. The remaining ITO is present in the form of melted droplets with varying sizes. VI. In the center of the focal spot, where the local intensity is the highest, there is no ITO left, only the underlying glass substrate is present. All these surface morphologies and the corresponding threshold peak intensities are summarized in Table 1.

Table 1. Different morphologies formed on the ITO and glass substrate surface and the corresponding threshold peak intensities.

<table>
<thead>
<tr>
<th>Area in Fig. 5</th>
<th>Peak intensity [W/cm²]</th>
<th>Surface morphology</th>
</tr>
</thead>
<tbody>
<tr>
<td>I.</td>
<td>2.1×10¹⁰</td>
<td>Cracks appear on the ITO surface due to thermal shock.</td>
</tr>
<tr>
<td>II.</td>
<td>7.1×10¹⁰</td>
<td>Nanometer sized craters and vertical periodic splinters.</td>
</tr>
<tr>
<td>III.</td>
<td>1.2×10¹¹</td>
<td>Separated periodic stripes with 200 – 240 nm periodicity.</td>
</tr>
<tr>
<td>IV.</td>
<td>1.6×10¹¹</td>
<td>Secondary, horizontal structure with 2 μm periodicity.</td>
</tr>
<tr>
<td>V.</td>
<td>2.6×10¹¹</td>
<td>Partly ablated ITO with melted droplets.</td>
</tr>
<tr>
<td>VI.</td>
<td>3.2×10¹¹</td>
<td>Ablated ITO, periodically structured glass surface.</td>
</tr>
</tbody>
</table>

It can be noticed that the glass surface is also periodically structured. This surface morphology is more distinguishable in the tilted SEM images with higher magnification, as shown in Fig. 5(b). In areas where the ITO became ablated the underlying glass substrate reveals its structured surface. The subwavelength periodicity of this pattern is comparable to the periodicity of the ITO.

To gather more information about the generated surface structures, we performed element analysis around the laser-treated areas. A 10 kV electron accelerating voltage was used for the sake of achieving a sufficient X-ray yield for all EDS lines (that all lie in the < 4 keV regime) and to keep the incidence depth of the electron beam relatively low. The typical excitation volume under the above-mentioned circumstances is around 0.2 μm³, which means that the composition information is averaged over this volume. Taking into account the limit above, we performed a line scan on the structured area generated by illuminating the sample 1 s with 2.4 μm wavelength, 2 × 10¹¹ W/cm² peak intensity pulses.
Fig. 6. a) Element analysis results obtained by a line scan on the laser treated area. The dashed blue line shows the line path. b) Local composition of the different components on the surface along the scan line.

Fig. 6. shows the line scan path and the obtained relative density of elements along the scan based on the detected electrons originating from the listed shells. It can be seen that approaching the center of the focal spot, the Si concentration starts to oscillate as the ITO becomes periodically ablated and the underlying glass becomes uncoated. At the same time, in an opposite phase, the In and Sn concentrations also oscillate showing the same effect. Where the local density of the ITO components is higher, the Si EDS signal originating from the glass substrate underneath becomes lower. This clearly shows the periodic ablation from the surface, creating the secondary structure with 2 µm periodicity.

4. Electromagnetic FDTD simulations

Despite the diverse experimental conditions of previous studies and our investigations, the appearing HSFLs have very similar properties both regarding the orientation and the periodicity. This suggests that it is more likely the ITO itself (and its properties) that determines the structure formation and not the wavelength/duration of the applied laser pulses.

ITO layers have an initially rough structure, which was studied with an AFM before any LIPSS experiment took place. Although the average roughness is not very high (rms roughness < 5 nm), the microroughness of the surface has a similar characteristic length to the period of the observed LIPSS structure. Fig. 7(a) shows a 3D visualization of the surface, while in b) three lineouts of the scanned area are presented.

Fig 7. a) 3D visualization of the surface based on AFM data. b) Lineouts of the scanned area. Characteristic period of the initial surface structures is 200–400 nm.
During the experiments, the interaction of the incident light with the initial structure of the irradiated material can lead to field localization in the pits of the rough surface. These pits of the surface may act as seeds for more prominent structural changes or even material removal [11].

To investigate the possible field localization, the distribution of the electric field along the surface of the ITO has to be calculated. For our calculations, we applied the Lumerical FDTD Solutions software. The source properties (bandwidth, temporal length, polarization) were set to be the same as of the laser pulses during the experiment. For taking into account the cumulative effect of multiple laser pulses, the optical properties of the ITO layer [17] were slightly modified based on the changes of carrier concentration and mobility reported by Wang et al [18]. For being able to monitor the effect of the surface roughness, AFM images taken from the surface of the ITO layer were directly introduced to the simulations. Volume of the FDTD unit cell was 5 µm x 5 µm x 1 µm and the spatial resolution near the surface of the ITO was set to 1 nm. Distribution of the electric field was monitored inside the ITO and field distribution maps were averaged over the top 20 nm depth of the layer. This averaged electric field patterns belonging to the applied wavelengths (1.6 µm, 2.0 µm and 2.4 µm) are plotted in Fig. 8 (a-c) (values are normalized). These figures can give indication on the formation of the HSFL structures, since the spatial domains exhibiting the largest local fields correspond to the structures/pits of the rough surface. Furthermore, if the electric field pattern is Fourier-transformed, the vertical orientation of the high intensity domains is clearly visible (note the bright areas located along the horizontal axis in the insets of Fig. 8(a-c)). The periodicity of these vertical domains varies between 200 and 500 nm matching nicely to the periodicity of the rough surface based on the AFM lineouts (c. f. Fig. 7). Since the local intensity is larger along these domains, these are the zones where the material modification such as ablation is likely to take place after the energy deposition, in accordance with the experimentally observed HSFL.

![Fig 8. Normalized average electric field distribution along the rough surface of the ITO layer using a) 1.6 µm, b) 2 µm and c) 2.4 µm illumination wavelength. Insets: FFT-spectra of the intensity distribution show the vertical periodicity clearly with characteristic length ranging between 200 and 500 nm. d)-f) Normalized values of the absorbed power inside the ITO layer along a line section for wavelengths 1.6 µm, 2 µm and 2.4 µm, respectively. Note that the line section is the same as the top panel of Fig. 7 b).](image-url)
Other indication for the connection between initial surface roughness and the periodic structure can be provided when the absorbed energy is calculated. Intensity values are proportional to the absorbed energy:

\[ P_{\text{abs}} = -0.5 \omega |\mathbf{E}|^2 \text{Im}(\varepsilon), \]

where \( \omega \) is the angular frequency of the illumination, \( \mathbf{E} \) is the electric field and \( \varepsilon \) is the dielectric function of the ITO at the given angular frequency value. Fig. 8(d-f) show the normalized values of the absorbed power inside the ITO layer along a line section.

Positions of regions encountering the maximum absorbed energy correspond to the pits on the ITO surface. These patterns of maximum absorbed energy define precisely the thermally affected zones, where the material modification takes place with the highest probability [12]. Considering the intensity maps and the pattern of the absorbed energy, it can be concluded, that during our experiments, it is most likely the initial roughness of the ITO layer, and the field localization in the pits of this rough surface that governs the formation of the HSFL structures.

5. Conclusions

We performed experiments in which we used femtosecond pulses in the infrared region with three different wavelengths to generate LIPSS on an ITO thin film. We observed primary HSFLs with periodicity between 200 and 240 nm with an orientation perpendicular to the laser polarization. We also obtained LSFLs parallel to the laser polarization with 2 \( \mu \text{m} \) periodicity, which we investigated with element analysis unfolding the periodic concentration of the surface material components. We observed that the periodicity of the generated surface structure’s is independent of the incident wavelength. This led us to the conclusion, that it is more likely the ITO itself (and its properties) that determines the structure formation. FDTD simulations based on AFM measurements were conducted, that confirmed our hypothesis about the origin of the LIPSS formations. We concluded that the initial surface roughness of the ITO layer with modified optical properties, and the field localization in the pits lead to a periodic absorption of the laser pulse energy that creates the periodic structures and even periodic material ablation from the substrate.
References


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